

## **AMENDMENTS TO THE SPECIFICATION:**

Please replace the paragraph beginning on page 4, line 15 of the Substitute Specification with the following amended paragraph:

Stable polymers, doped glasses, sequences of dielectric layers, highly doped semiconductors, narrow-band semiconductors, metals, etc. Pursuant to the invention, thermal decoupling is furthermore provided between detectors 5a, 5b and first substrate 4. For this purpose, a cavity, for example, is provided between detectors 5a, 5b and first substrate 4, as indicated in Figure 2 by reference numeral 6. A surface micro-mechanical technique is employed, for instance, to produce such a cavity 6 or such a cavern 6. For such techniques, porous silicon is used in partial regions of first substrate 4. Subsequently, the porous silicon is rearranged in such a manner that a lower region is provided, which forms a cavity, and that a higher region is provided, which forms a covering layer for first substrate 4 for accommodating detectors 5a, 5b. Furthermore, it is possible to produce such a cavity 6 using a known etching by xenon difluoride, ClF<sub>3</sub>, ClF<sub>5</sub>, by other interhalogen compounds which are able to etch substrate 4 isotropically, or by plasma-activated NF<sub>3</sub>. In addition to detectors 5a, 5b, ~~a heating conductor is~~ heating conductors 205a, 205b are also provided, pursuant to the invention, in the area of detectors 5a, 5b. ~~However, this is not as~~ shown in Figure 2. Such a heating conductor is provided in the inventive device for self-testing the sensor or the device. According to the present invention, a brief thermal pulse is produced by way of the heating conductor on the thermally decoupled area of detectors 5a, 5b. The function of temperature sensors 5a, 5b may thereby be tested.